



Wafer Based Temperature Metrology

Nov. 14th., 2013

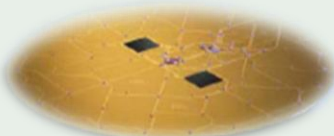
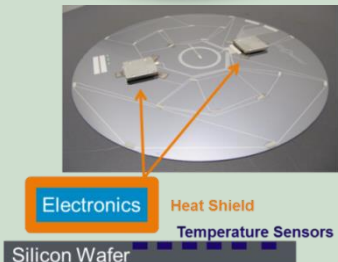
Dinh Chu, Giampietro Bieli, *Youxian Wen*; GEM/SensArray-VLSI Division



Agenda

- Introduction
 - SA Wireless Wafer Products
- Wafer based metrology
 - Accuracy & Stability
- Key use cases for Etch, Thin Film processes
 - Characterize thermal stability of process tool
 - Correlation between wafer temperature and critical process parameters, CDs
 - Matching of wafer temperature and thermal budget
 - Diagnosis of process and process tools
- Summary

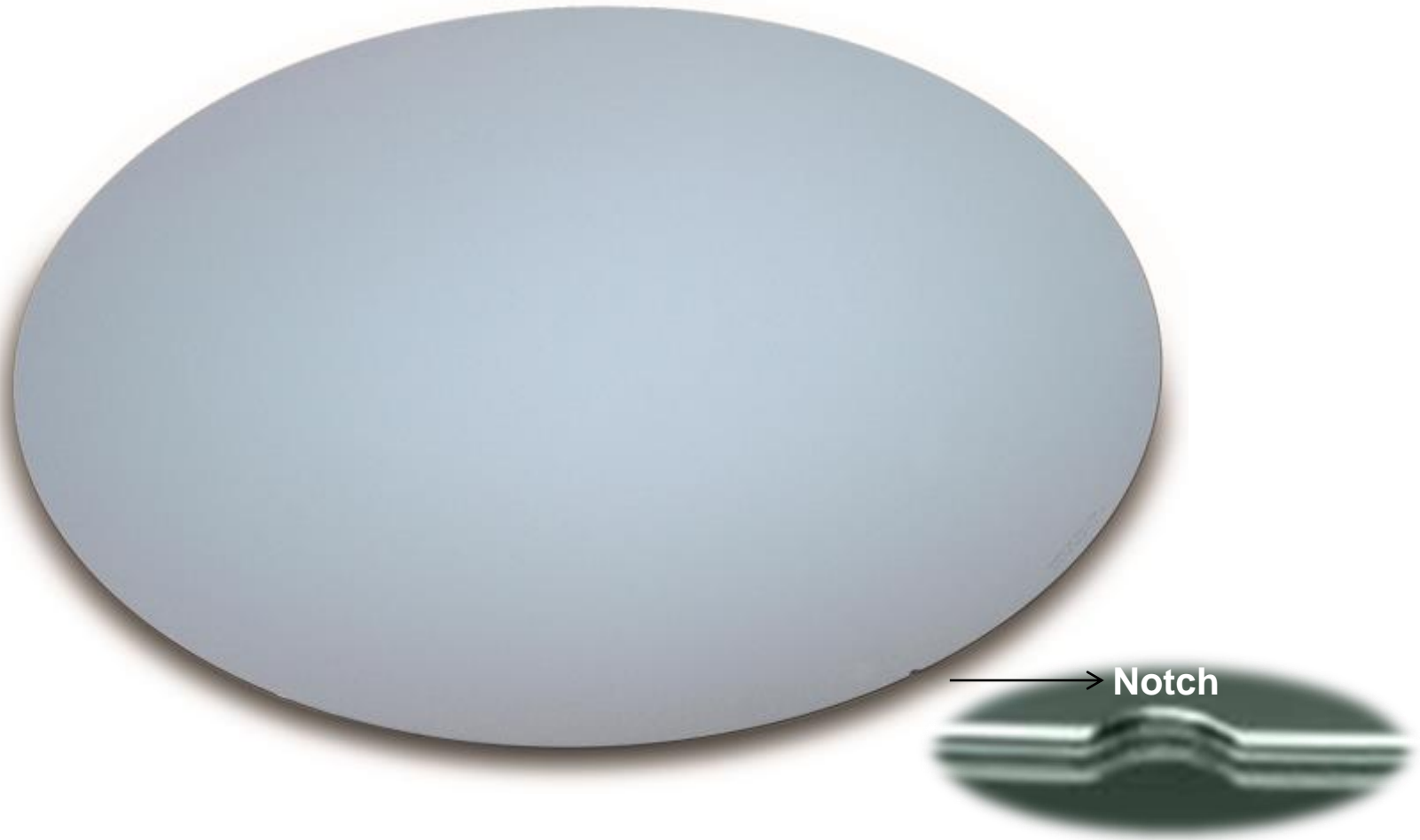
Key Wireless Temperature Wafers

Wireless Wafers		Spec.	Process
ST	Si cover	20~24°C ±0.05°C; 0.03°C 65 Sensors; 775um	Scanner
ET ET-SE	Sensors, electronics, battery	20~140°C ±0.2°C; 0.25°C 65 Sensors (Edge Dense); 1.2mm	Dry Etch Implantation
WT-LP	Si substrate	15~140°C ±0.5°C; 0.5°C 65 Sensors, 775um	Wet Etch Clean
Integrated Wafer		20-145°C ±0.1°C; 0.1°C 65 Sensors; 1.3mm	Clean Track Room Atmosphere
HT-350 XP		25~350°C 21 Sensors ±1.0°C; ≤0.6°C Plasma Off <6mm	Thin Film Strip

Metrology Tools
An enabler, and/or part of a Process Solution

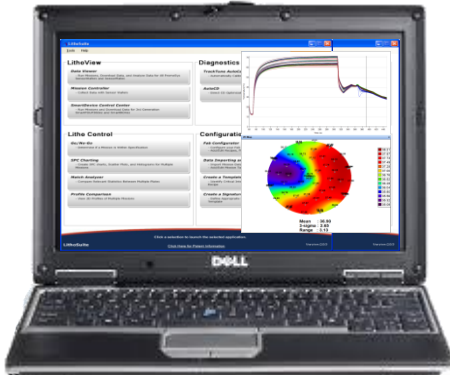
SensArray Integral Wafer Technology

Proprietary Sensor Solutions >160 Patents



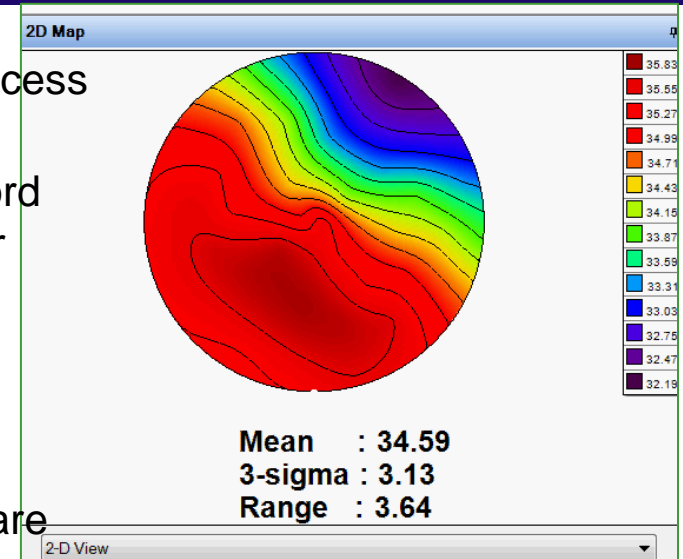
SensArray Wireless in-situ SensorWafer System

Measure and record in-situ wafer temperature up to 4Hz

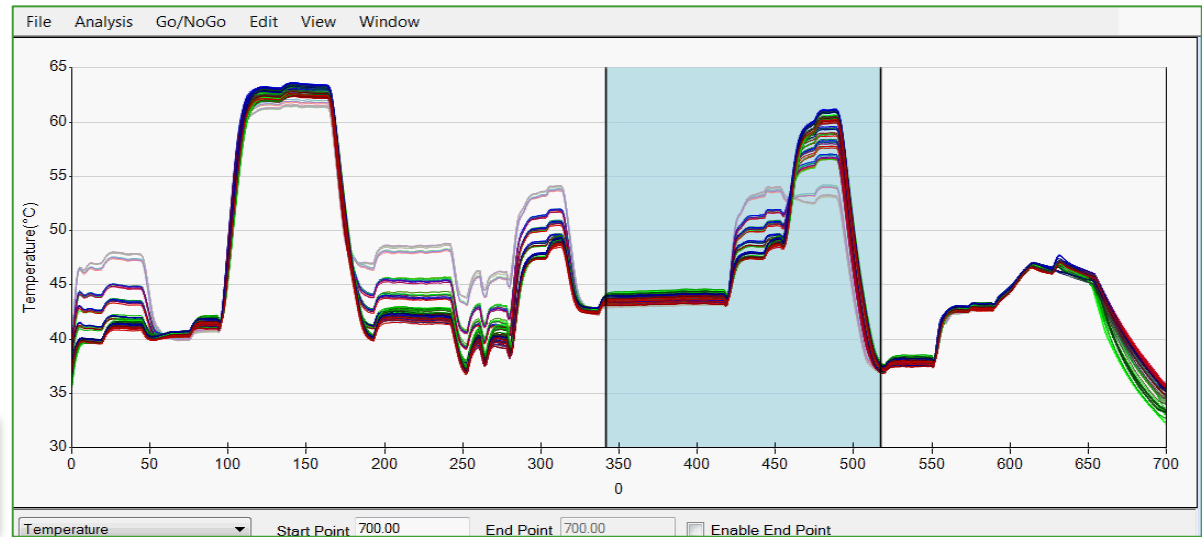


**SAT Control and Analysis
Software Version 2.6**

- Create Mission using process recipe
- Launch Mission and record temperature on the wafer while in a chamber
- Download data from the BaseStation
- Analyze data using the SensArray system software



**BaseStation 300Z
Communication & Charging**



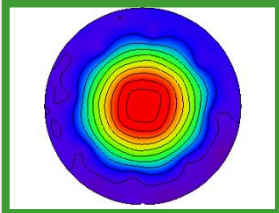
SensArray Core Value Proposition

Enhancing Process Equipment ROI Across the Fab

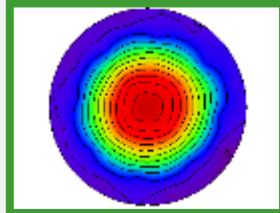
Tool Matching

EtchTemp-SE

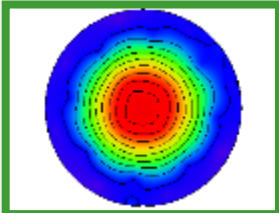
Tool A
Ch1



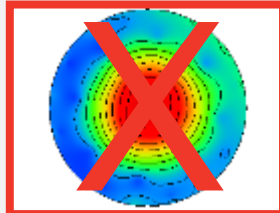
Tool A
Ch2



Tool B
Ch1



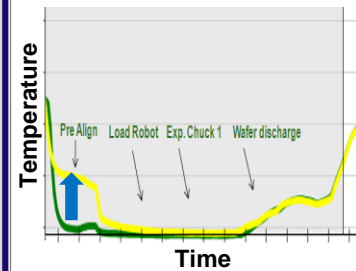
Tool B
Ch2



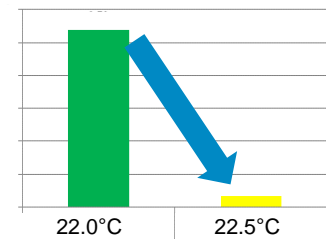
Troubleshooting

ScannerTemp

Scanner Temp Profile

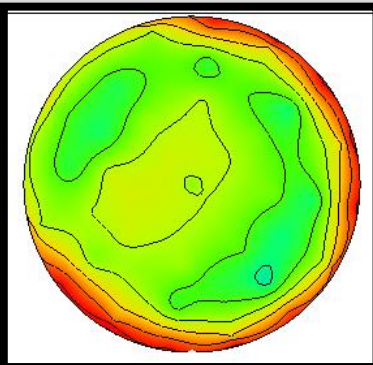


Overlay Shift

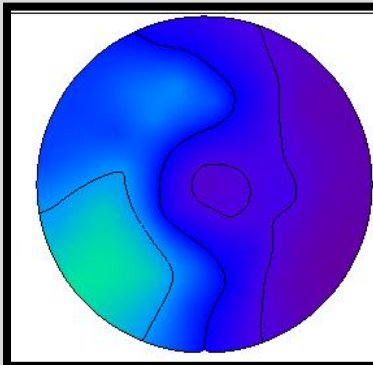


Process Characterization

WetTemp-LP



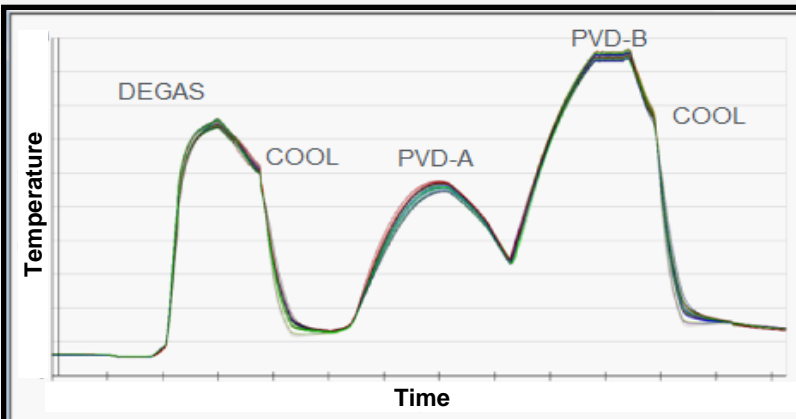
Process Condition A



Process Condition B

Multi Temp/Chamber Optimization

HighTemp-350



Key Use Cases

- Equipment Engineers

- Calibration/Qualification
- Thermal Stability
- Thermal Transient (Ramping)
- WiW uniformity
- C2C and T2T Matching

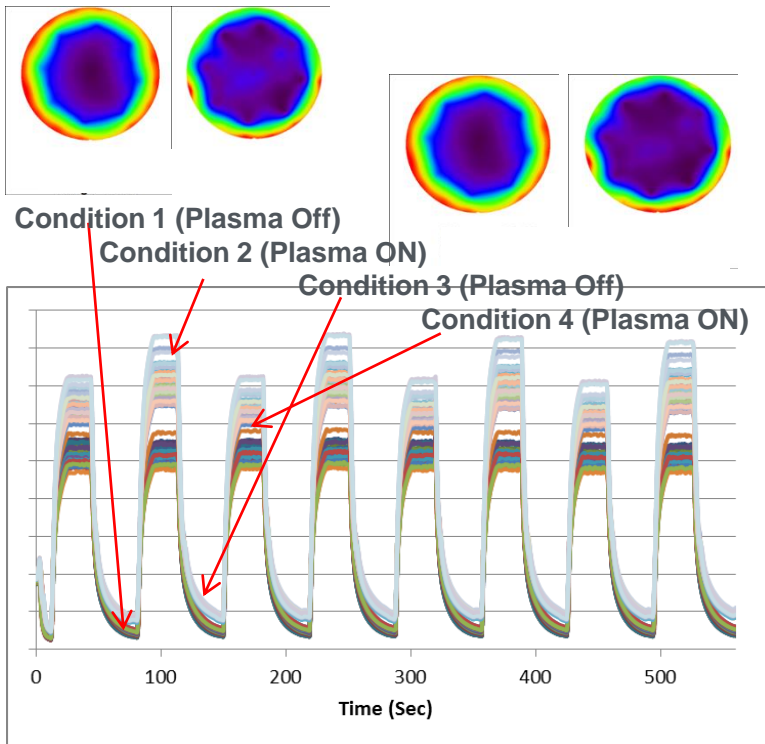
- How accurate is ?
- How stable is ?
- How fast is ?
- How uniform is ?
- How much variation is?

- Process Engineers

- Process Development
 - Effect of process knobs, i.e. temperature, power, chemistry, etc.
 - Allowable process window, i.e. range of temperature vs. process parametrics
 - Process Optimization & Integration
 - Duration between process steps
 - Thermal history
- How sensitive is?
 - How optimal Temp & Duration are?

Etch Temp Use Cases in additional to ESC Cal

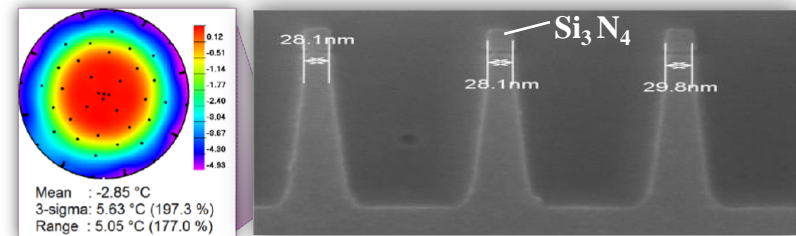
- Thermal Stability & Uniformity of Process Tool



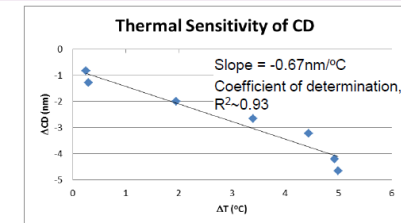
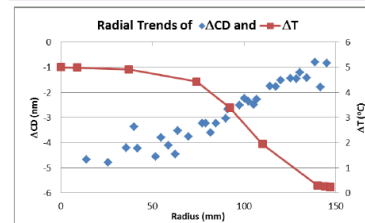
- Thermal Sensitivity of Process

CD and Wafer T Difference for Equal and Gradient T_{ESC}

Wafer Temp Difference between Gradient and Equal T_{ESC}



Radial Trends of ΔCD and ΔT



Temperature change of 1°C leads to a Dense CD change of ~ 0.7 nm

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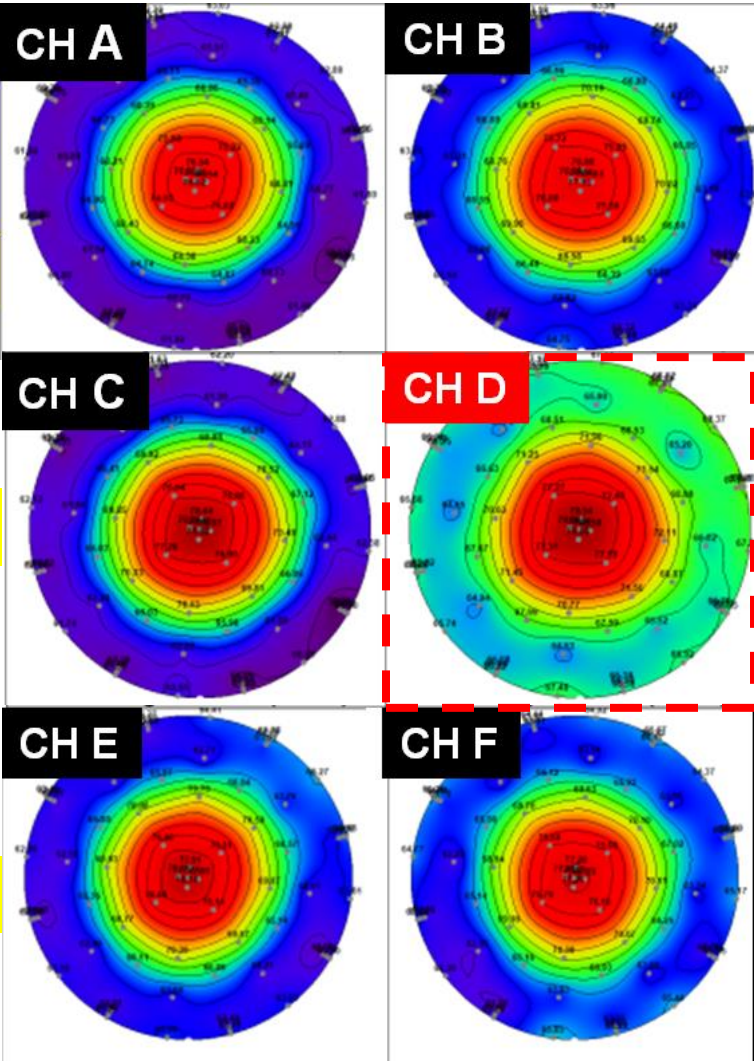
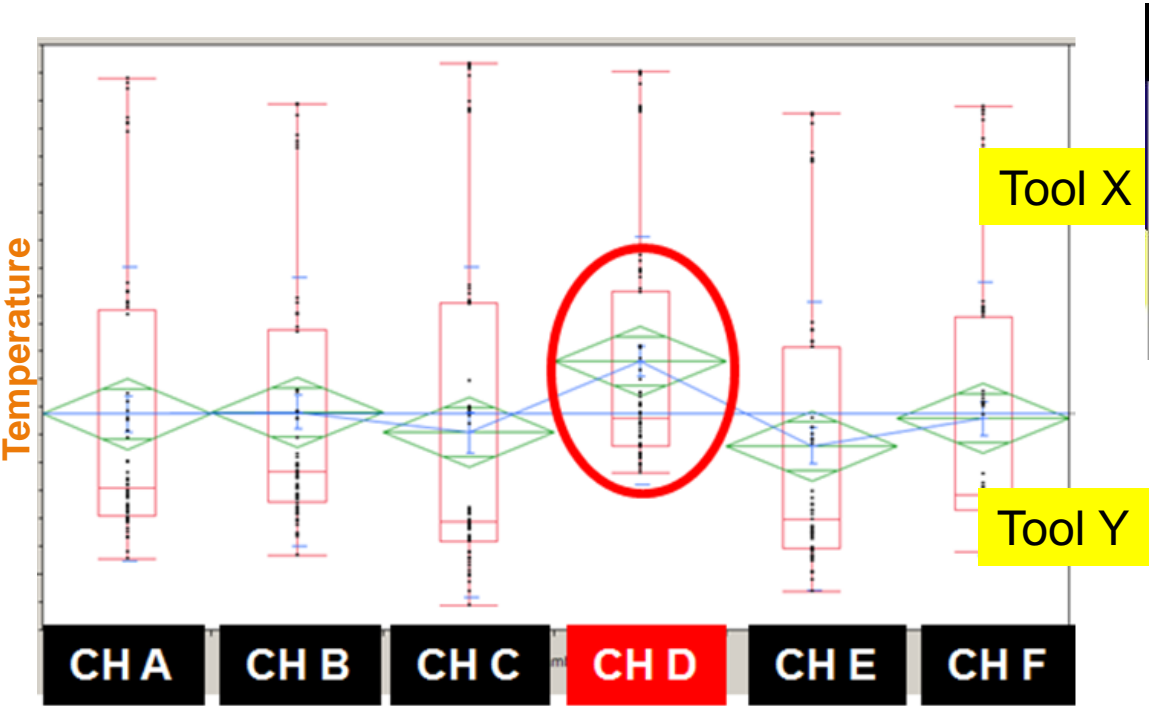
A.P. MILENIN

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Wafer Based Temperature Metrology for
Development & Optimization of Equipment & Process

Chamber Matching

STI Etch – High CD correlates to higher temp



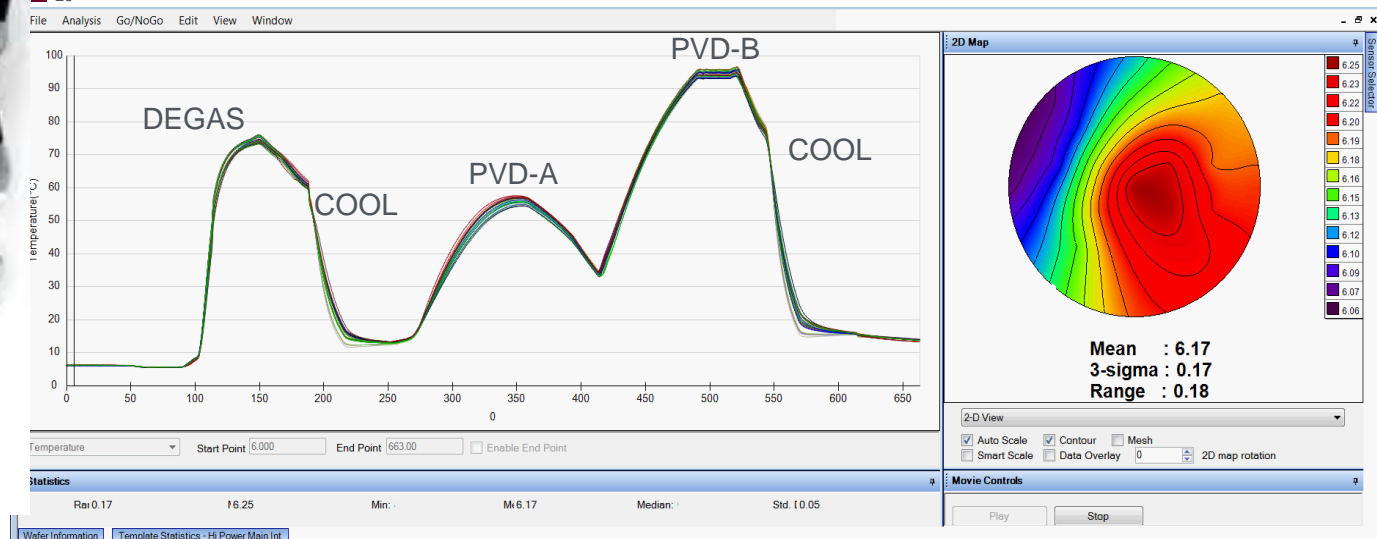
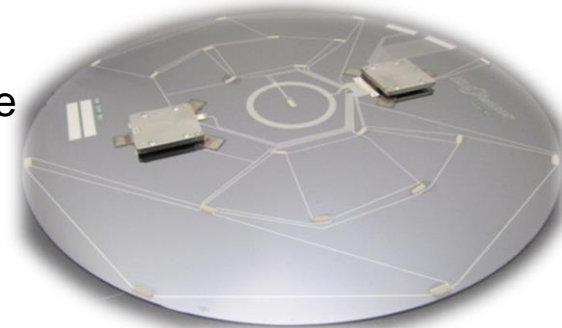
CH D shows higher temperature resulting in higher CD

Tool Z

HighTemp-350 Multi-Chamber Thermal Profiling



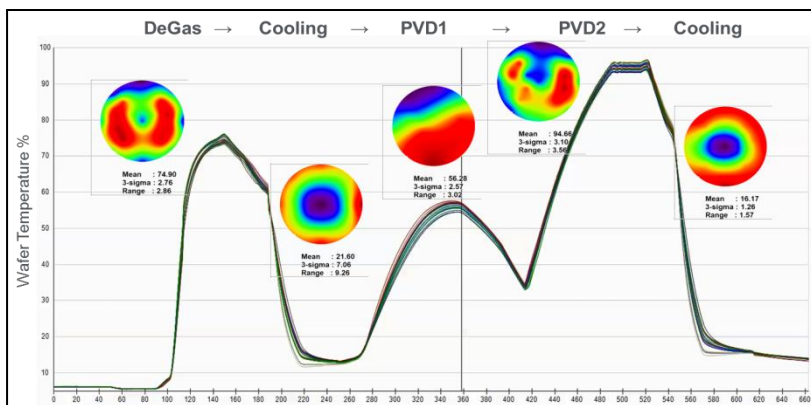
- Provide temporal & spatial temperature information beyond the current 140°C limitation
- Insulate temperature-sensitive components from extreme heat during time-limited missions



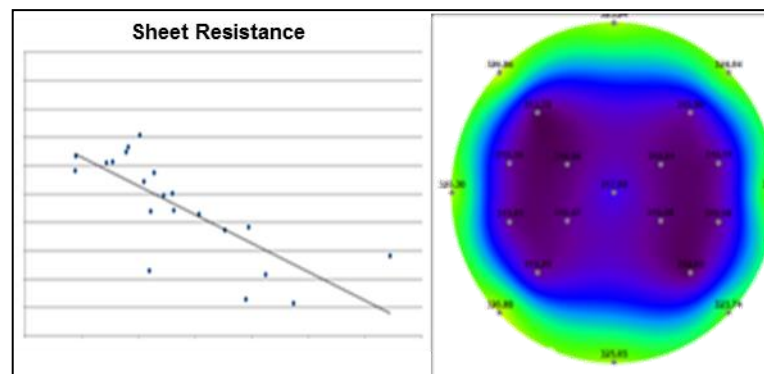
Cluster-tool thermal characterization not available by any other means

High Temp 350XP for Thin Film

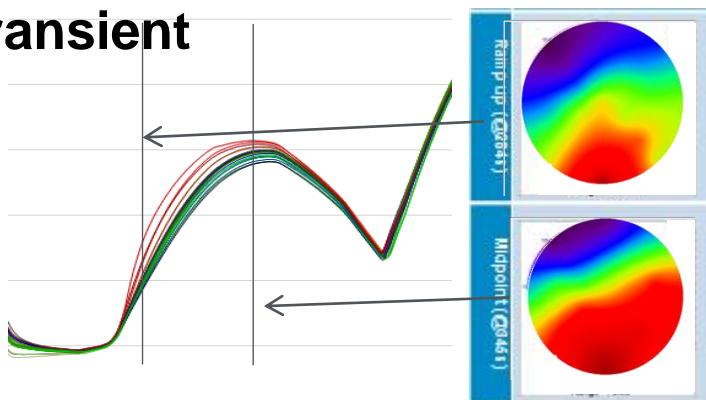
Integration



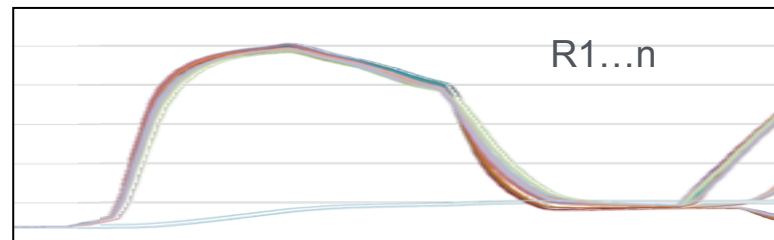
Thermal Sensitivity



Transient

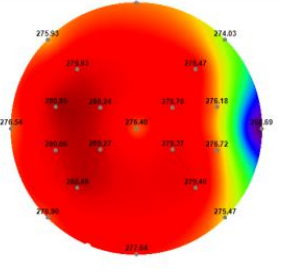
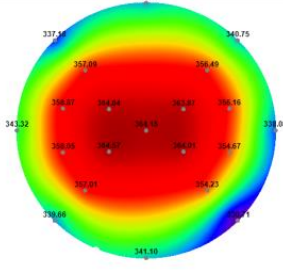
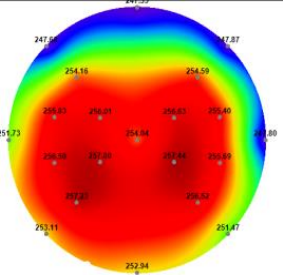
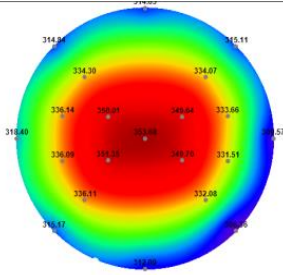


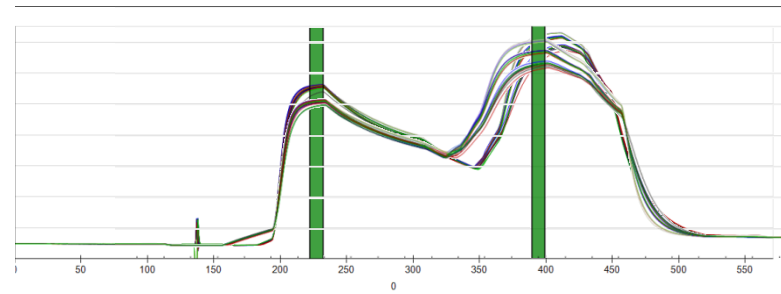
Thermal Stability



High Temp-350 enables process tuning based on wafer temperature

For Tool – Tool (chamber-chamber) Matching

Tools	A	B	Δ
Degas			
Mean			13.8
Range	14.2	10.1	
PVD			
Mean			21.4
Range	33.9	47.3	



- Both Chambers in Tool B are cooler than of Tool A
- Different cold spots between two degas chambers
- Larger temperature range in the PVD chamber of tool B than that of tool A
- Longer duration in PVD of tool B over tool A**
 - Different thermal budget**

Summary

- A metrology solution for characterizing and/or monitoring process tools
 - Thermal stability, uniformity, accuracy, matching, and throughput of all $\leq 350^{\circ}\text{C}$
- A metrology tool for process development & optimization
 - Effect of process knobs.
 - Thermal Sensitivity
 - Allowable process window
 - Duration of each and between process steps
 - Thermal budget

